


INT-A-PAK Power Module Thyristor/Diode, 300 A



INT-A-PAK

FEATURES

- Electrically isolated base plate
- 3000 V_{RMS} isolating voltage
- Industrial standard package
- Simplified mechanical designs, rapid assembly
- High surge capability
- Large creepage distances
- UL approved file E78996 
- Compliant to RoHS directive 2002/95/EC


**RoHS
COMPLIANT**
PRODUCT SUMMARY

$I_{T(AV)}$	300 A
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APPLICATIONS

- Battery chargers
- Welders
- Power converters
- Alternators

MAJOR RATINGS AND CHARACTERISTICS

SYMBOL	CHARACTERISTICS	VALUES	UNITS
V_{DRM}/V_{RRM}		800	V
$I_{T(AV)}$	53 °C	300	A
I_{TSM}	50 Hz	6500	A
	60 Hz	6900	
I^2t	50 Hz	214	kA ² s
	60 Hz	195	
$I^2\sqrt{t}$		2140	kA ² √s
T_J	Range	- 40 to 140	°C

ELECTRICAL SPECIFICATIONS
VOLTAGE RATINGS

TYPE NUMBER	V_{RRM}/V_{DRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V_{RSM}/V_{DSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I_{RRM}/I_{DRM} AT 125 °C mA
VSKL300-08PbF	800	900	50

ON-STATE CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average on-state current at case temperature	$I_{T(AV)}$	180° conduction half sine wave		300	A	
				53	°C	
Maximum RMS on-state current	$I_{T(RMS)}$	As AC switch		116	A	
Maximum peak, one-cycle on-state, non-repetitive surge current	I_{TSM}	t = 10 ms	No voltage reapplied	6600		
		t = 8.3 ms	No voltage reapplied	6900		
		t = 10 ms	100 % V_{RRM} reapplied	5500		
		t = 8.3 ms	100 % V_{RRM} reapplied	5800		
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reapplied	214		kA ² s
		t = 8.3 ms	No voltage reapplied	195		
		t = 10 ms	100 % V_{RRM} reapplied	151		
		t = 8.3 ms	100 % V_{RRM} reapplied	138		
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 ms to 10 ms, no voltage reapplied		2140	kA ² √s	
Low level value of threshold voltage	$V_{T(TO)1}$	(16.7 % $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$), T_J maximum		0.796	V	
High level value of threshold voltage	$V_{T(TO)2}$	(I > $\pi \times I_{T(AV)}$), T_J maximum		0.868		
Low level value on-state slope resistance	r_{t1}	(16.7 % $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$), T_J maximum		0.972	mΩ	
High level value on-state slope resistance	r_{t2}	(I > $\pi \times I_{T(AV)}$), T_J maximum		0.88		
Maximum on-state voltage drop	V_{TM}	$T_J = 25\text{ °C}$, 500 A I_{pk}	SCR	1.35	V	
	V_{FM}		DIODE	1.20		

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Typical delay time	t_d	Gate current 1 A, $dI_g/dt = 1\text{ A}/\mu\text{s}$ $V_d = 0.67\% V_{DRM}$, $T_J = 25\text{ °C}$		1.0	μs
Typical turn-off time	t_q	$I_{TM} = 300\text{ A}$, $T_J = T_J$ maximum, $dI/dt = 20\text{ A}/\mu\text{s}$, $V_R = 50\text{ V}$ $dV/dt = 20\text{ V}/\mu\text{s}$, Gate 0 V 100 Ω, $t_p = 500\text{ μs}$		100	

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 67 % rated V_{DRM}		500	V/μs
Maximum peak reverse and off-state leakage current	I_{DRM} , I_{RRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied		50	mA
RMS insulation voltage	V_{INS}	50 Hz, circuit to base, all terminal shorted, t = 1 s		3000	V



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TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms	10.0	W
Maximum average gate power	$P_{G(AV)}$	$T_J = T_J$ maximum, $f = 50$ Hz, $d\% = 50$	2.0	
Maximum peak positive gate current	I_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms	3.0	A
Maximum required DC gate voltage to trigger	V_{GT}	$T_J = 25$ °C Anode supply: 12 V resistive load	3	V
Maximum required DC gate current to trigger	I_{GT}		200	mA
Maximum holding current	I_H		600	
Maximum peak positive gate voltage	$+V_{GM}$	$T_J = T_J$ maximum, $t_p \leq 5$ ms	20	V
Maximum peak negative gate voltage	$-V_{GM}$		5.0	
DC gate voltage not to trigger	V_{GD}	$T_J = T_J$ maximum	0.30	V
DC gate current not to trigger	I_{GD}	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V_{DRM} anode to cathode applied	10	mA
Maximum non-repetitive rate of rise of turned-on current	di/dt	Gate drive 20 V, 20 Ω , $t_r \leq 1$ μ s $T_J = T_J$ maximum, anode voltage $\leq 80\%$ V_{DRM}	1000	A/ μ s

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction operating temperature range	T_J		- 40 to 140	°C
Maximum storage temperature range	T_{Stg}		- 40 to 150	
Maximum thermal resistance, junction to case per junction	R_{thJC}	DC operation	0.19	K/W
Maximum thermal resistance, case to heatsink per module	R_{thCS}	Mounting surface smooth, flat and greased	0.035	
Mounting torque $\pm 10\%$	IAP to heatsink busbar to IAP	A mounting compound is recommended and the torque should be rechecked after a period of 3 hours to allow for the spread of the compound. Lubricated threads.	4 to 6	Nm
Approximate weight			500	g
			17.8	oz.
Case style			INT-A-PAK	

ΔR CONDUCTION PER JUNCTION											
DEVICES	SINUSOIDAL CONDUCTION AT T_J MAXIMUM					RECTANGULAR CONDUCTION AT T_J MAXIMUM					UNITS
	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	
VSKL300	0.019	0.022	0.028	0.041	0.068	0.013	0.023	0.031	0.043	0.069	K/W

Note

- Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

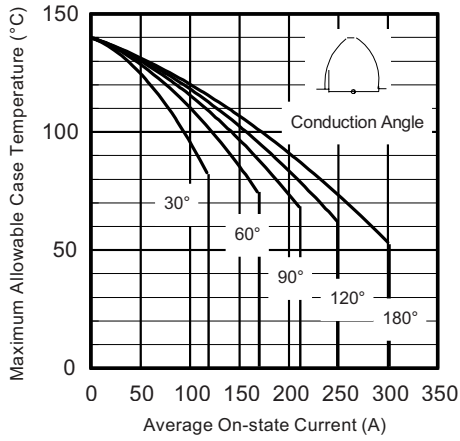


Fig. 1 - Current Ratings Characteristics

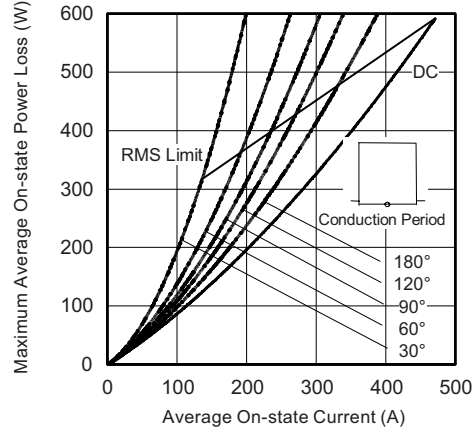


Fig. 4 - On-State Power Loss Characteristics

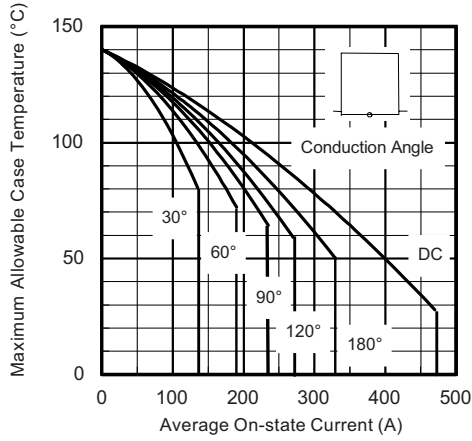


Fig. 2 - Current Ratings Characteristics

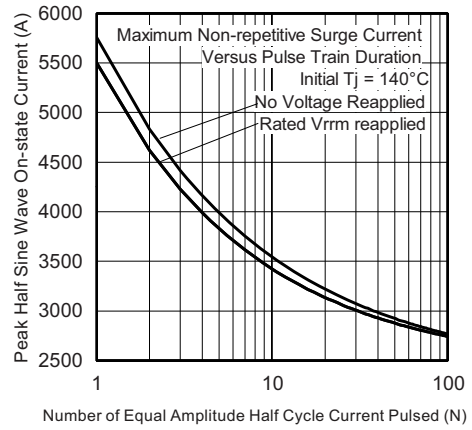


Fig. 5 - Maximum Non-Repetitive Surge Current

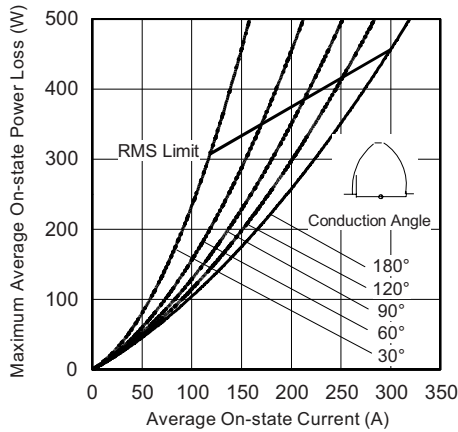


Fig. 3 - On-State Power Loss Characteristics

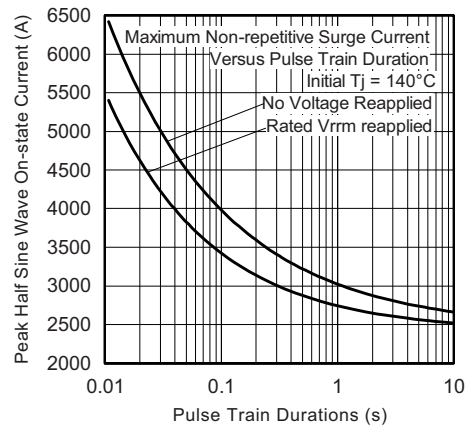


Fig. 6 - Maximum Non-Repetitive Surge Current

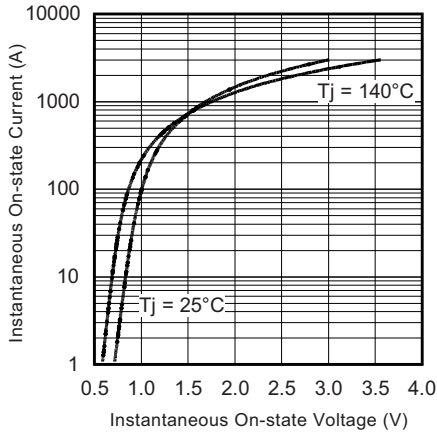


Fig. 7 - On-State Voltage Drop Characteristics (SCR)

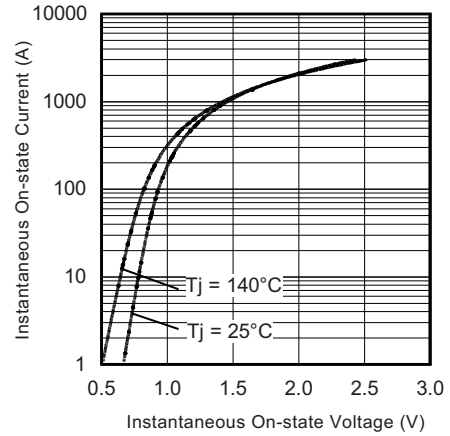
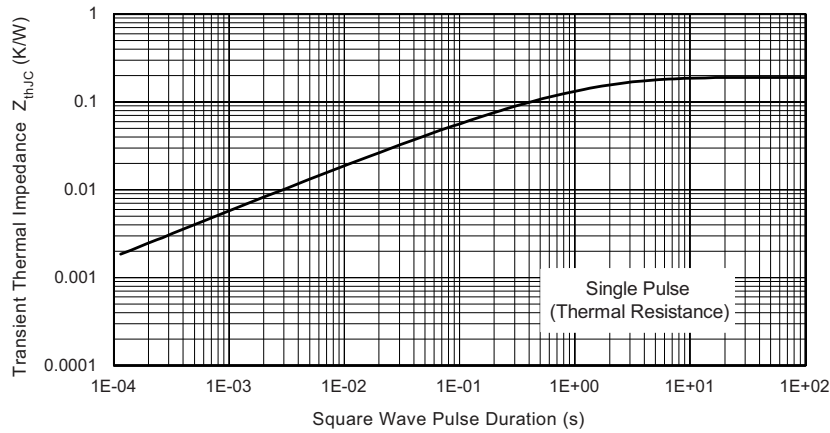


Fig. 8 - On-State Voltage Drop Characteristics (Diode)


 Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE

Device code	VSK	L	300	-	08	PbF
	①	②	③		④	⑤

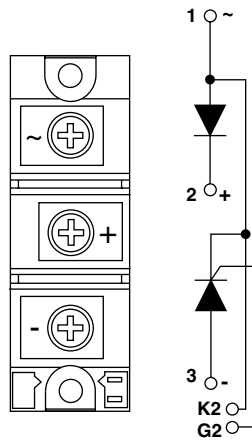
- 1** - Module type
- 2** - Circuit configuration (L = SCR/diode doubler negative control)
- 3** - Current rating (300 = 300 A)
- 4** - Voltage rating (08 = 800 V)
- 5** - PbF = Lead (Pb)-free

VSKL300-08PbF



Vishay High Power Products INT-A-PAK Power Module
Thyristor/Diode, 300 A

CIRCUIT CONFIGURATION



LINKS TO RELATED DOCUMENTS

Dimensions

www.vishay.com/doc?95010



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